Ferm i-surface topology and the e ects of intrinsic disorder in a class of charge-transfer salts containing magnetic ions, ⁰⁰-(BEDT-TTF)₄[(H₃O)M (C₂O₄)₃]Y

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We report high-eld m agnetotransport measurements on 00 -(BEDT-TTF)₄ [(H₃O)M (C₂O₄)₃]Y, where M = Ga, Cr and Fe and Y = C_5H_5N . We observe similar Shubnikov-de Haas oscillations in all compounds, attributable to four quasi-two-dimensional Ferm i-surface pockets, the largest of which corresponds to a cross-sectional area 8:5% of the Brillouin zone. The cross-sectional areas of the pockets are in agreem ent with the expectations for a compensated sem in etal, and the corresponding e ective m asses are me, rather small compared to those of other BEDT-TTF salts. A part from the case of the sm allest Ferm i-surface pocket, varying the M ion seems to have little e ect on the overall Ferm i-surface topology or on the e ective masses. Despite the fact that all samples show quantum oscillations at low temperatures, indicative of Ferm i liquid behavior, the sam ple- and tem perature-dependence of the interlayer resistivity suggest that these systems are intrinsically inhom ogeneous. It is thought that intrinsic tendency to disorder in the anions and/or the ethylene groups of the BEDT-TTF m olecules leads to the coexistence of insulating and m etallic states at low temperatures; comparison with other charge-transfer salts suggests that this might be a rather general phenom enon. A notional phase diagram is given for the general family of $^{\circ\circ-}$ (BEDT-TTF)4 [(H 30)M (C 204)3] Y salts, which exhibits several marked sim ilarities with that of the (BEDT-TTF)₂X superconductors.

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I. IN TRODUCTION

Superconducting charge-transfer salts of the molecule BEDT-TTF have attracted considerable experimental and theoretical interest because of their complex pressure-tem perature (P,T) phase diagram s, som e of which are super cially similar to those of the \high- T_c " cuprate superconductors^{1,2,3}. For example, the superconducting phase in the -(BEDT-TTF)2X salts is in close proximity to an antiferrom agnetic insulator^{4,5,6} and/or M ott insulator⁷; it is also surrounded by other unusual states^{4,5}, including what has been termed a \bad m etal"7. Recent m agnetisation8, therm al expansion¹⁰ and resistivity⁹ experim ents suggest that this \bad metal" may in fact represent the coexistence of Ferm iliquid-like and insulating phases. The presence of both metallic and insulating states at low temperatures is probably related to progressive freezing-in of disorder associated with the term inal ethylene-groups of BEDT -TTF (which can adopt either a \staggered" or \eclipsed" con guration) and/or with the anions, $X^{10,11,12,13,14}$. As yet there is no strong theoretical concurrence on the mechanism for superconductivity in the BEDT-TTF

salts^{3,15}, with electron-electron interactions, spin uctuations¹⁶, charge uctuations¹⁷ and electron-phonon interactions¹⁸ under consideration. It is therefore unclear as to whether the mixed insulating/m etallic phase referred to above is a prerequisite for or a hindrance to superconductivity. However, a recent paper has pointed out the sensitivity of the superconductivity in BEDT-TTF salts to non-m agnetic im purities and disorder, suggesting that this is evidence for d-wave superconductivity¹⁹.

In order to address som e of these issues we have studied a new family of charge-transfer salts of the form 0 -(BEDT-TTF)₄[(H₃O)M (C₂O₄)₃] Y, where M is a magnetic [Cr³⁺ (S = 3=2), Fe³⁺ (S = 5=2)] or nonmagnetic [Ga³⁺ (S = 0)] ion and Y is a solvent molecule such as C₅H₅N (pyridine), C₆H₅CN (benzonitrile) or C₆H₅NO₂ (nitrobenzene). Y essentially acts as a tem plate molecule, helping to stabilize the structure; its size and electronegativity a ect the unit cell volume, and the amount of disorder in the system 20,21,22,23,24,25 . The unit-cellvolume is also a ected by changing the M ion inside the tris(oxalate) structure^{21,22,24,25}. Furtherm ore, a subsidiary motive for varying M is to search for potential role form agnetism in the mechanism for superconductivity²⁰. In this context, the magnetic charge-transfer salt $-(BETS)_2FeC \ l_4^{26,27}$ has been found to exhibit a eldinduced superconducting state in elds > 17 T.W hilst these data appear to be explicable by the Jaccarino-Peter compensation e ect^{26,28,29}, others have suggested that the Fe ions play some role in the superconducting state^{27,30}.



FIG.1: M agnetic- eld dependence of the interplane resistivity, zz for $^{\rm (O)}-({\rm BED\,T}-{\rm T\,T\,F})_4\,[({\rm H}_3\,O\,)M~(C_2\,O_4\,)_3]$ Y samples containing di erent Y m olecules and transition m etal ions M . D ata are shifted vertically for clarity. Salts with (a) $Y=C_6\,H_5\,N\,O_2$ or (b) Y = $C_6\,H_5\,C\,N$ typically exhibit superconductivity, negative m agnetoresistance and a simple set of Shubnikov-de H aas oscillations. By contrast, the (c) Y = $C_5\,N_5\,N$ (pyridine) salt shows no superconductivity, positive m agnetoresistance and a complex series of Shubnikov-de H aas oscillations; this is entirely typical of the salts containing pyridine.

Although there are many detailed di erences between individual samples, the $^{(0)}-(B E D T - T T F)_4 [(H_3 O) M (C_2 O_4)_3] Y$ salts show two distinct classes of low-temperature behavior, as summarised in Fig. 1, which shows the interlayer magnetoresistivity $_{zz}$ (see Section II) of three samples at a temperature T = 0.50 K. Salts with $Y = C_6 H_5 \text{CN}$ (benzonitrile)

or $C_6H_5NO_2$ (nitrobenzene) are superconductors^{20,23}. At tem peratures above the superconducting-to-norm al transition, they tend to exhibit negative magnetoresistance, on which is superimposed one or two series of Shubnikov-de Haas oscillations of relatively low frequency²³. On the other hand, salts with Y = C_5H_5N are not superconducting; they exhibit positive magnetoresistance, and display a complex mixture of higher-frequency Shubnikov-de H aas oscillations. In this paper we shall concentrate on the Y = C_5N_5N salts, deriving their Ferm i-surface parameters and quasiparticle scattering rates; the superconductors with Y = C_6H_5CN or $C_6H_5NO_2$ are described in detail in another $paper^{23}$. However, in deriving a general phase diagram (Section V) we shall discuss the latter superconducting materials in general terms alongside the $Y = C_5H_5N$ salts.

This paper is organised as follows. Experim ental details are given in Section II; relevant structural details and the behavior of the ⁰⁰-(BEDT-TTF)₄ [(H_3O)M (C_2O_4)₃] GH_5N samples on cooling from room to cryogenic temperatures are given in Section III, which also outlines the mechanism swhich introduce disorder. Magnetoresistance data are analysed in Section IV; the Shubnikov-de Haas oscillations suggest that there are four Ferm i-surface pockets, the areas of which obey the additive relationship expected for a com pensated sem in etal. The results are discussed in Section V; this Section contains a notional phase diagram for the 00 -(BEDT-TTF)₄ [(H₃O)M (C₂O₄)₃] Y salts which shows the in uence of unit cell size and disorder, and which is compared with an equivalent phase diagram for the (BEDT-TTF), X salts. A summary is given in Section VI.

II. EXPERIMENTAL DETAILS

 00 -(BEDT-TTF)₄ [(H₃O)M (C₂O₄)₃] Y samples The were grown using electrocrystallisation techniques as described elsewhere^{20,21,22}; they are generally 1 1 0:2 mm³ hexagonal platelets or needles. It is possible to deduce the upper and lower faces that are parallel to the highly-conducting quasi-two-dimensional planes by visual inspection. Electrical contacts were made to these surfaces by using graphite paint to attach 12 m platinum wires. The interlayer (magneto) resistance R_{zz} / zz (Ref. 3) was measured using standard four-term inal actechniques. This involves driving the current and m easuring the voltage between pairs of contacts on the upper and low er surfaces³. M agnetoresistance experim ents were carried out in quasistatic elds provided by a superconductive m agnet in O xford and a 33 T Bitter coil at NHMFL Tallahassee. The crystals were mounted in a³H e cryostat which allowed rotation to all possible orientations in magnetic eld; sam ple orientation is de ned by the angle between the direction of the magnetic eld and the norm alto the quasi-two dimensional planes

М /Ү	a(A)	b(A)	с(А)		V (A ³)	T (K)	R ef.
$Ga/C_6H_5NO_2$	10,278	19.873	35.043	93.423	7145,2	100	21
$C r/C_6 H_5 N O_2$	10,283	19.917	34.939	93,299	7144.4	150	25
$Fe/C_6H_5NO_2$	10,273	19.949	35.030	92.969	7169.6	120	25
Cr/C ₆ H ₅ CN	10,240	19.965	34.905	93.69	7121.6	120	24
Fe/C ₆ H ₅ CN	10,232	20.043	34.972	93.25	7157	120	20
Ga/C_5H_5N	10,258	19.701	34.951	93,366	7051.9	120	21
Fe/C ₅ H ₅ N	10,267	19.845	34.907	93,223	7101.0	150	22

and the azim uthal angle . Sam ple currents between 1 and 25 A were used at typical frequencies 18-300 Hz. A lthough around 20 crystals have been studied, in this paper we shall focus on two or three typical sam ples of each salt; sam ples are distinguished by the consistent use of a label (e.g. M = Cr, Sam ple A).

III. STRUCTURAL CONSIDERATIONS AND DISORDER IN THE LOW -TEMPERATURE PHASE

A. Structure and band lling

Figure 2 shows a projection of the crystal ⁰⁰-(BEDTstructure along the a axis of the $TTF)_4[(H_3O)M (C_2O_4)_3]$ GH₅N salts, and Table I gives the lattice parameters (around 120 K) for all compounds studied in this paper and in Ref. 23. The structure consists of alternating BEDT-TTF and anion layers, the latter containing the metal tris(oxalate) $[M (C_2O_4)_3]^3$, the ion H_3O^+ and the solvent molecule, Y. The molecules in the anion layer lie in a \honeycomb" arrangement with alternate $H_{3}O^{+}$ and metal oxalates giving an approximately hexagonal network of cavities in which the solvent molecule Y lies. The solvent molecule helps to stabilize the structure; the plane of phenyl ring makes an angle of 32 36 to the plane of the oxalate $ayer^{22,2\overline{4},25}$. The metal ion M is octahedrally co-ordinated to the oxalate ligands; the oxygen atoms on the oxalates are weakly bonded to the hydrogen atom s on the term inal ethylene groups of the BEDT-TTF molecules, acting to pull these together. The BEDT-TTF molecules adopt the packing arrangement in the ab planes, in which they form roughly orthogonal stacks. The crystallographic structure of our compounds is monoclinic (see Table I) with the (ab) conducting planes at a distance of d = c=2from each other, as shown in Figure 2^{22} .

By far the shortest S-S distances are within the cation planes, leading to a predominantly two-dimensional bandstructure^{20,31}. Each BEDT-TTF molecule is expected to donate half an electron, leaving two holes per unit cell. Band structure calculations based on the



FIG. 2: Monoclinic crystal structure of $^{\rm (O-(BED\,T-TTF)_4}[(H_3O\,)M~(C_2O_4)_3]\ GH_5N$ projected along the a axis 21 .

room temperature crystallographic data suggest these salts should be compensated sem in etals, with a Ferm i surface consisting of quasi-two-dimensional electron and hole pockets of approximately equal area ³¹. A lthough BEDT-TTF salts and their relatives are frequently compensated sem in etals³, the electron-like Ferm i-surface component is often a pair of open sheets; a closed electron pocket is relatively unusual, but it was found in $^{\circ}$ -(BEDO-TTF)₂ReO 4 ${}_{\rm EO}^{32}$.

The interlayer transfer integrals will be less straightforward to calculate in the $^{\rm OD}-(B\,ED\,T-T\,T\,F\,)_4\,[(H_{\rm 3}O\,)M~(C_{\rm 2}O_{\rm 4})_{\rm 3}]$ Y salts; the planes of the BEDT-TTF molecules in adjacent layers (as well as those of the anion layers) are twisted with respect to each other by 62 $\,$ 2, an unusual feature in BEDT-TTF salts^{20,24}.

B. Disorder mechanisms

The 00 -(BEDT-TTF)₄ [(H₃O)M (C₂O₄)₃] Y salts are prone to structural disorder primarily because the terminal ethylene groups (CH_2CH_2) of the BEDT-TTF molecules are able to adopt dierent con gurations (twisted/staggered or eclipsed) depending on how they interact with the anion layer^{21,22}. M oreover, since C_5H_5N is smaller than the other tem plating Y molecules, it does not 11 the whole of the hexagonal cavity. Changing the solvent molecule from $Y = C_6H_5NO_2$ to Y =C₅H₅N induces additional structural freedom, leading to disorder in around one quarter of the term inal ethylene groups^{21,22}. As a result, the ethylene groups are the dom inant cause of both static and dynam ic disorder at high tem peratures, and static disorder below 90 K, the tem perature around which the two di erent con gurations phase salts 10,11,12 . are frozen in "²¹, as found in the

The C₅H₅N m olecule can also introduce disorder by adopting two di erent orientations in the anion layer. By contrast, the other solvents, $Y = C_6H_5NO_2$ and $Y = C_6H_5CN$, lock into one ordered con guration²¹.

Having discussed the various mechanisms for disorder, we shall now examine how disorder is manifested in the resistivity of the samples.



Temperature (T) dependence of the nor-FIG. 3: m alized interplane resistance $R_{\,z\,z}$ (T)/R $_{z\,z}$ (286 K) in zero magnetic eld for dierent samples of $^{\rm (0)}-(\!B\,E\,D\,T\,-\!T\,T\,F\,)_4$ [(H $_3O$)M (C $_2O$ $_4$)_3] GH $_5N$ with ⁰⁰-(BEDT-(a) M = Ga (sample A) (the inset shows $TTF)_4[(H_3O)M (C_2O_4)_3] Y with M = Ga, Y = GH_5NO_2$ for comparison), (b) M = Cr sample B (the inset shows M = Crsample A) and (c) M = Fe (samples A and B). The arrows indicate the tem peratures described in the text.

C. The tem perature dependence of the resistivity

The temperature dependence of the normalized interplane resistance, R_{zz} (T)= R_{zz} (286 K), for ve typical ⁰⁰-(BEDT-TTF)4[(H₃O)M (C₂O₄)₃] GH_5N sam ples is shown in Figure 3; for comparison, equivalent data for M = Ga, Y = C₆H₅NO₂ are displayed in the inset. W hilst many of the features in the data are quite sam pleor cooling-rate-dependent, all of the sam ples (M = Ga, Cr, Fe) are consistent in displaying a transition from m etallic-type behavior (positive dR $_{zz}=dT$) to insulating-type behavior (negative dR $_{zz}=dT$) at $T_{M\ I}$ 150 K . Values of $T_{M\ I}$ are listed in Table II.

The minimum in resistance at $T_{M I}$ may represent the onset of a possible form of density-wave state. Quasitwo-dimensional conductors in which the Ferm i surface is completely gapped by a density wave exhibit a resistivity that rises by several orders of magnitude as the tem perature falls, as found for $(BEDT-TTF)_3Cb$ 2H $_2$ O 33). By contrast, the resistance of the 00 -(BEDT-TTF)₄ [(H_3O)M (C_2O_4)₃] GH_5N salts (shown in Figure 3) only increases by a factor 1:5 3. The latter behavior is sim ilar to that of quasi-two-dimensional conductors in which a density wave only partially nests the Ferm i surface, leaving behind residual Ferm i-surface pockets; examples include the Mo bronzes³⁴ and $(BEDT-TTF)_2 KHg(SCN)_4^{35}$. In such cases, the conductivity is a convolution of a m etallic component, typically varying as a power-law in tem perature (due to the unnested portions of the Ferm isurface) and an insulating component with an activated temperature dependence (due to the energy gap of the density-wave state) 34 . The exact form of the resistivity depends on which component dom inates. An alternative scenario that could potentially lead to sim ilar resistivity behavior is the segregation of the sample into insulating and metallic domains 36 , as also proposed for the (BEDT-TTF),X salts (see Ref. 9 and references therein). In Section IV we shall see that the Ferm i-surface topology is more complicated than that predicted by the bandstructure calculations, which may be additional evidence that the transition at $T_{M\ I}$ is associated with the form ation of a density-wave.

All of the $Y = C_5H_5N$ crystals also consistently exhibit a feature at a lower tem perature, T_p 60 80 K (shown in Fig. 3). However, depending on the sample, this is manifested either as a change from insulating-to metallic-type behavior (M = Ga, all samples, M = Cr, sample B, M = Fe sample A), or as merely a shoulder on a resistivity that continues to increase with decreasing temperature (M = Cr, sample A, M = Fe, sam ple B). Such a feature is also indicative of a number of contributions to the conductivity acting in parallel. for example, it is possible to reproduce the behavior of M = Cr sample B between 60 K and $T_{M I}$ using a resistor network model that combines metallic (resistivity / Tⁿ, with n 2) and therm ally-activated com po-1 nents / exp ($E_A = k_B T$) (see also R ef. 37). A lthough the exact values obtained depend on the details of the resistor network m odel used, the values of E_A obtained from tting data between T_p and T_M I showed a consistent increase from $M = Fe (E_A)$ 170 220 K) through M = Ga (E_A 300 K) to M = Cr (E_A 400 500 K), i.e. the activation energy EA increases with decreasing unit cellvolume (see Table I).

The features discussed thus far do not seem to depend on sample cooling rate. By contrast, in all ve M = Cr samples studied, there is an additional peak in the resistivity at T_d 200 270 K, the appearance and

tem perature of which both depend on the sam ple cooling rate. By contrast, sam ples with M = Ga, Fe only exhibit a small in ection at T_d . At the lowest tem peratures, R_{zz} (T)= R_{zz} (286 K) values ranging from around 0.5 (M = Fe, sam ple A) to 7 (M = Cr, sam ple A) are obtained (Fig. 3); the actual value reached seems m ore dependent on the sam ple batch rather than the identity of the M ion (e.g. com pare M = Cr sam ples A and B). This points to a prom inent role for disorder in determ ining the low-tem perature resistive behavior of the O -(BEDT-TTF)₄ [(H₃O)M (C₂O₄)₃] GH₅N salts.

As T tends to zero, the resistivity of M = Cr sam pleB drops quite sharply, although zero resistance is never attained. A similar drop in resistance for M = Ga below 2 K, which was destroyed by an applied eld of 0.16 T, was previously reported as evidence for superconductivity²¹. How ever, none of the M = Ga sam ples studied in the present work exhibited such a feature. This is possibly related to the recent observation that superconductivity in the BEDT-TTF salts is very sensitive to disorder and non-m agnetic in purities¹⁹.

On the other hand, a robust superconducting state is stabilized below $T_c = 7 \text{ K}$ for M = Ga and $Y = C_6H_5NO_2$ (as shown in the inset of Figure 3(a)) and for M = Fe and $Y = C_6H_5CN$ (Figure 1(b) and Ref. 20). For completeness, note that both of the latter superconducting salts show a single m etal-insulator transition (see inset of Figure 3(a)) similar to that observed at $T_{M \ I}$ in the $Y = C_5H_5N$ salts. However, for the superconducting salts $T_{M \ I}$ seem as some what sample dependent; values ranging from $T_{M \ I} = 68 \text{ K}^{23}$ to $T_{M \ I} = 160 - 180 \text{ K}^{21}$ have been reported for the M = Ga, $Y = C_6H_5NO_2$ salt.

To sum marise this section, the resistivities of the $^{\circ\circ}$ -(BEDT-TTF)₄ [(H₃O)M (C₂O₄)₃] GH₅N salts exhibit a com plex tem perature and sam ple dependence (Figure 3). The minimum in R_{zz} at T_{MI} is an intrinsic feature of all sam ples, and, by analogy with resistivity data from other quasi-two-dimensional systems, probably indicates the onset of a density-wave state. The form of the resistivity attem peratures just below this (including the peak at T_p) suggests m etallic and therm ally-activated contributions to the conductivity acting in parallel. At lower tem peratures, the behavior of the sam ples is much more divergent, with R_{zz} (T)= R_{zz} (286) values spread between 0:5 and 7 indicating an additional therm ally-activated process (or processes) which is (are) probably dependent on the degree of disorder within the samples. By contrast, the tem perature-dependent resistivity is rather simpler for the ⁰⁰-(BEDT-TTF)₄ [(H₃O)M (C₂O₄)₃] Y salts with $Y = C_6H_5NO_2$ and $Y = C_6H_5CN_2$. The dierence may be attributable to the higher degree of structural disorder possible in the $Y = C_5H_5N$ salts, resulting from the less constrained ethylene groups and greater rotational freedom of the Y molecule²¹. Similar electronic properties determined by the disordered anions (that lock into two di erent con gurations) were found for 00 -(BEDT-TTF)₂SF₂CHFCF₂SO₃³⁹, for which resistivity shows a metal-insulating transition near 190 K, com -

pared with the superconducting compound, $^{\rm CO}-(BED\,T-T\,T\,F)_2SF_2CF_2CF_2SO_3$ (T_c = 5:4 K), which has ordered anions⁴⁰.

IV. LOW -TEM PERATURE MAGNETORESISTANCE

A. Shubnikov-de H aas frequencies and Ferm i-surface pockets

Figure 4 show s the eld dependence ⁰⁰-(BEDTof R_{zz} for several sam ples of TTF)₄ [(H_3O)M (C_2O_4)₃] GH_5N with M = Ga, Cr and Fe measured at several temperatures between 0.50 K and 4.2 K. All samples exhibit Shubnikov-de H aas oscillations superim posed on a positive background Several frequencies are visible m agnetoresistance. in varying proportions. For example, the dominant series of oscillations for M = Cr is of relatively low frequency, whereas the dom inant oscillations for M =Ga, Fe are of a higher frequency. The amplitude of the oscillations varies slowly with tem perature, suggesting the corresponding e ective masses are not very large⁴¹.

No clear signature of superconductivity was observed either in the eld, angle or temperature dependence of R_{zz} when $Y = C_5H_5N$, in contrast to the situation in ⁽⁰⁾– (BEDT-TTF)₄ [(H₃O)M (C₂O₄)₃] Y salts having dierent solvents [as shown in Fig. 1 and inset of Figure 3 (a)].

In order to analyse the Shubnikov-de H aas oscillations, we de ne the oscillatory fraction of the m agnetoresistance,

$$\frac{R_{zz}}{R_{bg}} = \frac{R_{zz}}{R_{bg}} \cdot (1)$$

Here R_{bg} is the slow ly-varying background m agnetoresistance approximated by a polynomial in B. As long as $R_{zz}=R_{bg}$ 1, $R_{zz}=R_{bg}$ $_{zz}=_{bg}$, where the are equivalent terms in the conductivity^{41,47} ($_{zz}=_{bg}$ is the quantity dealt with in the Lifshitz-K osevich (LK) treatment of Shubnikov-de H aas oscillations⁴¹ used to extract e ective m asses and the scattering time of the quasiparticles). The $R_{zz}=R_{bg}$ values were processed using both the maximum entropy method (MEM) (1ter size = 200)⁴² and the Fast Fourier transform (FFT) usually over the eld range 7 32 T. The two methods give similar representations of the frequencies present, as shown in the right panel of Fig. 4.

W e identify four frequencies which occur consistently in all of the transforms over the complete temperature range (see Figures 4 and 5), and are similar in all 00 -(BEDT-TTF)₄ [(H₃O)M (C₂O₄)₃] GH₅N samples with M = Ga, Cr and Fe. These frequencies are F 50 T, F 98 T,F 293 38 86 308 T and F 345 353 T; the ranges cover the values observed in the di erent samples (see Table II). In addition, two other peaks, with frequencies F⁰ 190 206 T and 236 248 T, were observed less consistently in the F^{00}



FIG. 4: M agnetic eld dependence of the interplane resistance, R_{zz} , for ⁽⁰⁾-(BEDT-TTF)₄ [(H₃O)M (C₂O₄)₃] GH₅N sam ples M = Ga (sam ples A (a) and B (a')), M = Cr (sam ples A (b) and C (b')) and M = Fe (sam ples A (c) and B (c')), recorded between T = 0.5 4.2 K. The right panel [(a"), (b") and (c")] corresponds to the maximum entropy method (top solid lines) and Fast Fourier transform spectra (bottom solid lines) of the oscillatory component of the resistance, [($R_{zz} R_{bg}$)= R_{bg} , where R_{bg} is a polynomial t] over the eld range 7-32 T; the transform s correspond to the data from left panel at T = 0.5 K. The dashed vertical lines indicate the approximate positions of the frequencies discussed in the text.

transform s. The peak at very low frequencies (6 20 T) is an artifact of the subtraction of the background m agnetoresistance; its position and amplitude depends on whether R_{bg} was approximated by a second or fourth-order polynomial in B. In some cases, the peak at frequency F is superimposed on the ank of this feature, making a precise determination of the frequency di cult.

Because of their dependence on temperature (see below), magnetic-eld orientation (all frequencies vary as 1=cos, where is the angle between the magnetic eld and the normal to the quasi-two-dimensional planes⁴³) and their consistent appearance in the transforms, we attribute the Shubnikov-de H as frequencies F, F, F and F to the extrem al orbits about four independent quasi-two-dimensional Ferm i-surface pockets, which we label ; ; and . As for the other peaks, we note that as F⁰ 2F, it is likely to be a second harm onic of the oscillations due to the pocket.

The peak seen occasionally in the transforms at a frequency F⁰⁰ seems likely to result from frequencymixing e ects and it can be constructed using a variety of recipes (for example, F⁰⁰ F + 2F, F⁰⁰ F F, F⁰⁰ F F). Such frequency-mixing e ects in quasi-two-dimensional metals are often attributable to the chemical potential becoming pinned to relatively sharp Landau levels over restricted regions of magnetic eld (the so-called \chemical potential oscillation e ect" (CPOE))^{44,45}, which, in some cases, very complex mixed harmonics are generated⁴⁶. Another possibility which can generate a di erence frequency is the Stark Quantum Interference e ect^{47} ; this represents \interference" of two sem iclassical Ferm i-surface orbits between which tunnelling can occur. However, the oscillations due to the Stark Quantum Interference e ect are usually characterised by an apparent very light e ective mass; that is, their am plitude varies more slow ly with temperature than that of the oscillations due to the two \parent" orbits⁴⁸. The fact that, when present, the oscillations at F⁰⁰ are suppressed much more rapidly with increasing temperature than any of the possible parent frequencies suggests that CPOE is the more likely explanation⁴⁹.

At this point, it is worth recalling that the bandstructure calculations predict only two Ferm i-surface pockets, of equal area³¹, whereas the experim ental data suggest four pockets. There are several potential reasons for this di erence. Firstly, whilst extended Huckel calculations often give a reasonable qualitative description of the Ferm i surfaces of many BEDT-TTF salts³, ⁰⁰-phases have proved problem atic; slight di erthe ences in input parameters seem to result in wildlydi ering predicted topologies (see, for exam ple, the case ⁰⁰ (BEDT-TTF)₂AuBr₂⁵⁰). Secondly, the bandof structure calculations are based on structural measurem ents carried out at relatively high tem peratures²¹; contraction of the lattice could result in changes in the relative sizes of the various transfer integrals, leading to shifts in the bands with respect to the chem ical potential. Finally, the presence of a series of pockets could be a consequence of a Ferm i surface reconstruction determ ined by a possible charge-density wave at $T_{M I}$ of the ⁰⁰-(BEDT-TTF)₄ [(H₃O)M (C₂O₄)₃] GH₅N salts. Similar Ferm i-surface reconstructions have been suggested for other ⁰⁰ salts, including ⁰⁰-(BEDT-TTF)₂AuBr₂ (where a plethora of small Ferm i surface pockets results)⁵⁰, ⁰⁰-(BEDO-TTF)₂ReO₄ \downarrow O³² and ⁰⁰-(BEDT-TTF)₂SF₅CH₂CF₂SO₃, where it appears that the Ferm i-surface nesting is more e cient ⁵².

In spite of the larger number of Ferm i-surface pockets observed experimentally, there are some similarities with the calculated Fermi surface. First, the largest experimental pocket, , is of a similar crosssectional area (8:5% of the Brillouin cross-section) to the calculated pockets (8:1% of the Brillouin-zone cross-section)³¹. Secondly, as noted above, the $^{\circ\circ}$ - $(BEDT-TTF)_4$ [(H₃O)M (C₂O₄)₃] Y salts are expected to be quasi-two-dimensional compensated sem in etals in which the cross-sectional areas of the hole Ferm i-surface pockets should sum to the same value as the total crosssectional area of the electron Ferm i-surface pockets. W e note that F + F F + F to reasonable accuracy (Table II). This suggests that if and are electron (hole) pockets, then and will be hole- (electron-) like.

A though the Shubnikov-de Haas oscillation frequencies are generally similar for the three 00 -(BEDT-TTF)₄ [(H₃O)M (C₂O₄)₃] GH_5N salts, there are detail di erences depending on the ion M . For example, the F frequency of the M = Cr salts is consistently lower than that of the M = Ga and Fe compounds. The appearance of the Shubnikov-de Haas oscillations is also a ected by the M ion; the highest frequency oscillations (F) dom inate the spectra of the compounds with M = Ga and Fe, whereas that of the compounds with M = Cr is dominated by the low frequency, F (see Figures 4 and 5). This may be related to relatively small di erences in the scattering mechanisms, rather than some intrinsic e ect of the Cr^{3+} ion. Examples of sim ilar e ects were observed in magnetoresistance data for the low - eld, low -tem perature phases of -(BEDT-TTF)₂KHg(SCN)₄and $-(BEDT-TTF)_2THg(SCN)_4^{53}$. The relative am plitudes of the various Shubnikov-de H aas oscillation series vary from sample to sample, and batch to batch, with some series being undetectable in what is presumed to be the lower-quality samples, whilst being relatively strong in other crystals (see Sections 1 and 5 of Ref. 53 and references cited therein). A second example is ⁽⁰⁾ (BEDT-TTF), AuBr₂ for which com parison of the magnetic-quantum oscillation data from Refs. 50,54,55,56 shows that the relative amplitudes of the lower and higher-frequency oscillation series varies considerably from sample to sample.

For completeness, we mention that the superconducting salts, $Y = C_6H_5NO_2$ with M = Ga and Cr and $Y = C_6H_5CN$ with M = Fe show only two frequencies, with the low frequency in the range 47 55 T and the high frequency in the range 190 238 T²³.



FIG. 5: Fast Fourier transforms of Shubnikovde Haas oscillations for samples of $^{(0)}$ -(BEDT-TTF)₄[(H₃O)M (C₂O₄)₃] GH₅N. (a) M = Ga (B), (b) M = Cr (A) and (c) M = Fe recorded between T = 0.5 K and T = 4.2 K.

B. E ective m asses and D ingle tem peratures

A two-dimensional Lifshitz-Kosevich form ula^{57} has been used to extract the e ective masses m of the various Ferm i-surface pockets, where possible. The Fourier amplitude of each series of quantum oscillations is given by

$$A_{2D} / R_T R_D R_S;$$
 (2)

where $R_T = \frac{X}{\sinh(X)}$ is the tem perature dam ping term, $R_D = \exp - X \frac{T_D}{T}$ is the D ingle term (T_D is the D ingle tem perature) due to the broadening of the Landau levels caused by internal inhom ogeneities and X = $14.694 \frac{T}{B} \frac{m}{m_{e}}$.

The spin-splitting term $R_s = \cos \frac{1}{2} \frac{g m = m_e}{\cos(1)}$, where g is the elective g-factor, but is not considered here and it will be the subject of a future publication⁴³.

The Fourier am plitudes obtained over a eld window 7 32 T were tted to the R_T term of Eqn. 2, using around 8 di erent tem peratures covering the range 0.5 42 K (for consistency, a polynom ial of the same order was used to subtract the background m agnetoresistance for each sam ple). Figure 6 shows typical am plitudes and corresponding ts for the F series. All of the m values obtained for the di erent Ferm i-surface pockets are listed in Table II.

To the limit of experimental error the elective masses for the and pockets of the three salts are close to the free-electron mass, m_e . Whilst such values are light compared to the typical masses observed in $^{O}-(BEDT-TTF)_2SF_5CH_2CF_2SO_3^{52}$ or the and

phaseBEDT-TTF salts⁴⁷, they are not without precedent in charge-transfer salts^{32,33}. The e ective m asses of the pocket are som ew hat sm aller for the M = C r and $m_e=2$); however, in the case of the M = Fe salts (m G a salt, the e ective m ass seems rather larger. A part from this, there is yet no evidence that the magnetic mom ent on the 3d ions M = Cr and Fe has any e ect onthe e ective masses. This is in contrast to the study on -(BETS)₂FeCl₄, where it was proposed that spin uctuation e ects enhanced the e ective m ass⁵⁸. On the other hand, the elective mass in $-(BETS)_2Fe_xGa_1 \times Cl_4$ is not very much a ected by the presence of the magnetic ions but it is much larger than that in our compounds 4m_e²⁹). (

A further insight into the properties of our samples is given by the D ingle tem perature, T_D , which can be used to param eterise the scattering rate^{19,41}, the spatial potential uctuations or a combination of the two 9,19 . The T_D values for the pocket are listed in Table II; typical ts are shown in Fig. 6(b). Note that T_D is consistently larger for the compounds with M = Fe (T_D 4 K , corresponding to a scattering time of 0:3 ps) and is smaller for the salts with $M = Cr (T_D)$ 1:5 K, corre-0:8 ps). This di erence is visible even in sponding to the raw data, with fewer oscillations being visible for the M = Fe salt. A s both com pounds contain m agnetic ions, som e form of magnetic scattering (such as spin-disorder scattering⁵⁹) m ay be excluded as the reason for these differences; it is more likely to be related to the degree of nonm agnetic disorder present, determ ined by the anions and the solvent.

Interestingly, there is no apparent correlation between the values of R_{zz} (T)= R_{zz} (286 K) (see Figure 3) and the D ingle temperatures for each sample (Table II). For example, the sample with the largest R_{zz} (T)= R_{zz} (286 K) (7) (M = Cr, sample A) has a T_D which is a factor 2.2 sm aller than that of the sample with the sm allest R_{zz} (T)= R_{zz} (286 K) (0.5) (M = Fe, sample A). The



(a) Temperature dependence of the Fourier FIG. 6: ⁰⁰-(BEDTam plitude of the F frequency in TTF)₄ [(H_3O)M (C_2O_4)₃] GH₅N for dierent M. The solid line is a t to the data (points) using the R $_{\rm T}$ term of Eq.2 (solid line). The eld window was B = 7 32 T for the samples with M = Cr (sample A) and M = Fe (sample A) and B = 12 32 T for the sample with M = Ga(sam ple A). Data for dierent M are o set for clarity. (b) The corresponding D ingle plots (ln [A 2D sinh (X)=X] versus 1=B, where X = 14:695 m T=B) for the F frequency at 0:5 K. The solid line is a linear t to the data (points). Т The eld windows overlapped by less than 30%.

D ingle tem peratures extracted from Shubnikov-de H aas oscillations suggest that M = Cr sam ple A is of higher quality, whereas M = Fe sam ple A has the lower resistivity ratio. This strongly suggests that the sam ples are not of a uniform single phase at the lowest tem peratures but their overall properties probably represent a m ixture of m etallic and insulating dom ains. W ithin this m ixture, the m etallic dom ains m ay well be of quite high quality, as evidenced by the observation of Shubnikov-de H aas oscillations with a reasonably small D ingle tem perature.

Further support for such an idea is given by com – paring the values of R_{zz} (10 K)= R_{zz} (286 K) 0:5 7 seen in Fig. 3 with R_{zz} (10 K)= R_{zz} (286 K) 0:001 ob-

Pa	ram eters	M = G	Ga(A)	M =	Ga(B)	M = 0	Ga(C)	M =	Cr(A)	M =	Cr(B)	M = C	'r (L)	M =	Fe(A)	M = F	'e(B)	
F	(T)	48			50 49		39			38		40		45		45		
F	(T)	8	9	85		92		95		95		98		94		92		
F^{0}	(T)	205			{	{		1	190 190		.90	195		{		{		
F ⁰⁰	(T)	247		2	40	235			{	{		243		243		{		
F	(T)	29	92	2 296		297		2	96	286		305		307		305		
F	(T)	344		3	45	346		3	344		343		357		346		344	
m	(m _e)	{	[1:9	0:3	1:3	0:2	0:56	0:05	0:54	0:05	0:5	0:1	0:8	0:1	0 : 6	0:1	
m	(m _e)	0:56	0:05	0:51	0:05	0:62	0:05	0 : 63	0:05	0 : 62	0:05	ł	[0 : 68	0:05	0 : 76	0:05	
m	(m _e)	0 : 7	0:1	1:01	0:05	1:09	0:05		{	{		{		{		{		
m	(m _e)	0 : 98	0:05	0 : 95	0:05	0 : 93	0:05	1:04	0:05	0 : 98	0:05	0:9	0:1	0:9	0:1	1:1	0:1	
${\rm T}_{\rm D}$	(K)	2 : 7	0:1	2:3	0:2	1:7	0:2	1:8	0:1	1:4	02	2:5	0:5	4	0:5	42	0:1	
${\tt T}_{\tt M}$	ı(K)	138	2		{		-	142	1		{	120	20	150	2	153	2	

tained for the unambiguously metallic salt (BEDT-TTF)_2I_3³⁸. This great disparity is an indication that a large fraction of the quasiparticles in the ⁽⁰⁾-(BEDT-TTF)_4 [(H₃O)M (C₂O₄)_3] GH₅N salts that are mobile at room temperature do not contribute to the bulk conductivity at low temperatures. This loss of charge-carriers is presumably be related to the suggested density-wave transition at T_{M I} (which perhaps gaps part of the Ferm i surface) and to the subsequent \freezing out" of further quasiparticles (suggested by the negative dR_{zz}=dT values seen for several of the sam ples as shown in Figure 3) caused by disorder at low er temperatures.

V. DISCUSSION: PROPOSED PHASE DIAGRAM

The previous sections have described ⁰⁰-(BEDTof the transport properties TTF)₄ [(H_3O)M (C_2O_4)₃] GH_5N salts exhibiting a m etal-insulator transition at $T_{M I}$ (probably associated with a density-wave state) and Shubnikov-de Haas oscillations at low er tem peratures, indicative of a reasonably good metal. However, depending on the sample batch, the overall resistivity can be much greater than that at room temperature; the most likely explanation is that the sample consists of a mixture of metallic and insulating domains. The tendency for a particular region of the sample to remain metallic or become insulating may be linked to particular con gurations of the anion and/or ethylene groups possible in the 00 -(BEDT-TTF)₄[(H₃O)M (C₂O₄)₃] GH₅N salts (see the discussion of intrinsic disorder in Section III).

These ndings are sum marised in Figure 7(a), which shows a notional phase diagram for all of the $^{(0)}$ -(BEDT-TTF)₄ [(H₃O)M (C₂O₄)₃] Y salts as a function of \chem ical pressure" (= V=V), i.e. the fractional di erence in unit-cell volume of a particular salt from that of the M = Fe, Y = $C_{6}H_{5}NO_{2}$ compound, which has the largest unit cell. For comparison, Figure 7 (7) shows an analogous diagram for the (BEDT-TTF)X salts (after Ref. 9 based on Refs. 4,8,10). There are a num – ber of quite striking sim ilarities between the two phase diagram s.

- 1. The superconductivity is suppressed by the reduction in volume of the unit cell. The suppression of superconductivity is accompanied by the increasingly \m etallic" character of both families of materials; in the ⁰⁰-(BEDT-TTF)₄ [(H₃O)M (C₂O₄)₃] Y salts, this is evidenced by the increase in the number and size of Ferm isurface pockets observed (two for $Y = C_6 H_5 NO_2$, C_6H_5CN , four, generally larger ones for Y = C₅H₅N); in the -(BEDT-TTF)₂X salts this shows up as an increase in the Shubnikov-de H aas oscillation frequencies and the low -frequency optical conductivity³. This trend is con m ed by hydrostatic pressure measurements of the superconducting "-BEDT-TTF₄ [(H_3O)Ga(C_2O_4)₃] Y salts, which showed that the superconductivity is destroyed and the number of Ferm i-surface pockets increased by increasing pressure 60 .
- 2. As the chem ical pressure increases, the suggested density-wave transitions (which occurs at $T_{M I}$ in the O -(BEDT-TTF)₄ [(H₃O)M (C₂O₄)₃] Y salts and at T in the (BEDT-TTF)₂X com pounds) increases in temperature, at least initially. In this context, recall that the characteristic activation energy E_A (Section III) also increases with chem ical pressure.
- 3. In both fam ilies, the superconducting state is surrounded by regions in which m etallic and insulating



⁰⁰-(BEDT-FIG. 7: (a) Notional phase diagram of the TTF)4[(H3O)M (C2O4)3] Y salts, using data from the current paper and from Ref. [23]. Solid circles correspond to the superconducting critical tem perature, T_c, open circles represent the metal-insulator transition, $T_{M\ I}$. The other tem peratures, T_p and T_d , are described in the text. Dierent phases are: SC = superconducting, DW -density wave, M m etallic, PM -param agnetic m etallic and I-insulating phase. The solid and dashed lines are guides to the eye. (b) Phase diagram of -(BEDT-TTF)2X including boundaries suggested by recent data \N otional pressure" com bines chem ical pressure caused by changing anion X and applied hydrostatic pressure; \0" is am bient pressure for -(BEDT-TTF)₂CuN(CN)₂Cl; the vertical lines are the ambient pressure positions of deuterated (left) and undeuterated (right) -(BEDT-TTF)₂Cu(NCS)₂ (after Ref. [9] based on Refs. [4,8,10]).

behavior $\cos x + DW + DW$ "phase (in the -phase salts after R ef.⁸).

The 00 -(BEDT-TTF)₄ [(H₃O)M (C₂O₄)₃] Y salts seem to emphasise two emerging them es in the physics of organic (super) conductors. Firstly, there have been a num ber of recent instances in which very high sam ple resistivity and phenom ena indicative of quasiparticle localisation (e.g. Anderson localisation⁶¹) and/or disorder⁶² coexist with e ects norm ally associated with \good m etals", such as Shubnikov-de Haas oscillations⁶³ or even superconductivity⁶¹. Secondly, there is experim ental evidence that the precursor to superconductivity m ay involve the coexistence of metallic and density-wave-like states (for exam ple ⁰⁰-(BEDT-TTF)₂SF₅CH₂CF₂SO₃⁵² or It has been suggested in the case of the phase salts that these phases exist in distinct \dom ains" or regions of the sample, the behavior of a particular dom ain being determ ined by local structural arrangem ents.

Finally, recent theoretical work has emphasised the role of disorder in the suppression of superconductivity in (BEDT-TTF) salts. Offen a measure of this disorder is derived from Shubnikov-de Haas-oscillation or cyclotron-resonance data¹⁹. The resistivity data indicate that disorder makes some regions of the sam ples prone to localisation and these regions contribute little to the low - tem perature conductivity. O ther regions remain m etallic and exhibit Shubnikov-de Haas oscillations, indicative of reasonably long scattering times and mean-free paths

300A and hence low disorder. Thus it is important to emphasise that Shubnikov-de H aas and cyclotron resonance data are only informative about the disorder in the m etallic regions of a sample (see also R ef. 9).

VI. SUMMARY

In conclusion we have studied the Ferm i-surface topology of $^{\rm (O)}-(B\,{\rm ED}\,T-T\,T\,F)_4\,[(H_3O\,)M\,(C_2O_4)_3\,]\,$ Y, (with M = Ga, Cr, Fe and Y = C_5H5N). All of the studied salts exhibit sim ilar Shubnikov-de H aas-oscillation spectra, which we attribute to four quasi-two-dimensional Ferm i-surface pockets. The cross-sectional areas of the pockets are in agreement with the expectations for a compensated sem in etal, and the corresponding e ective m asses are $m_e,$ rather sm all compared to those of other BEDT-TTF salts. A part from the case of the sm allest Ferm i-surface pocket, varying the M ion seems to have little e ect on the overall Ferm i-surface topology or on the e ective m asses.

Despite the fact that all samples show quantum oscillations at low temperatures, indicative of Ferm i liquid behavior, the sample- and temperature-dependence of the interlayer resistivity lead us to suggest that these systems are intrinsically inhom ogeneous. It is thought that intrinsic tendency to disorder in the anions and/or the ethylene groups of the BEDT-TTF m olecules leads to phase separation of the samples into insulating and m etallic states. Based on the data in this paper, and those from Ref.23, we have constructed a notional phase diagram for the $^{\rm O}-(B\,ED\,T\,-T\,T\,F\,)_4$ [(H $_3O$)M (C $_2O\,_4\,)_3$] Y salts which exhibits several similarities with that of the $(B\,ED\,T\,-T\,T\,F\,)_2X$ superconductors, and which could have larger in plications for other charge-transfer salts.

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